

## List of Publications by Citations

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

96  
papers

1,158  
citations

18  
h-index

31  
g-index

136  
ext. papers

1,478  
ext. citations

3.9  
avg, IF

4.11  
L-index

#	Paper	IF	Citations
96	Design of compact and smooth free-form optical system with uniform illuminance for LED source. <i>Optics Express</i> , <b>2010</b> , 18, 9055-63	3.3	177
95	Understanding efficiency droop effect in InGaN/GaN multiple-quantum-well blue light-emitting diodes with different degree of carrier localization. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 201112	3.4	94
94	Epidermal Inorganic Optoelectronics for Blood Oxygen Measurement. <i>Advanced Healthcare Materials</i> , <b>2017</b> , 6, 1601013	10.1	60
93	Analytical expression of sampled Bragg gratings with chirp in the sampling period and its application in dispersion management design in a WDM system. <i>IEEE Photonics Technology Letters</i> , <b>2000</b> , 12, 1013-1015	2.2	60
92	Integrated High-Q Crystalline AlN Microresonators for Broadband Kerr and Raman Frequency Combs. <i>ACS Photonics</i> , <b>2018</b> , 5, 1943-1950	6.3	49
91	Van der Waals Epitaxy of III-Nitride Semiconductors Based on 2D Materials for Flexible Applications. <i>Advanced Materials</i> , <b>2020</b> , 32, e1903407	24	47
90	An improved carrier rate model to evaluate internal quantum efficiency and analyze efficiency droop origin of InGaN based light-emitting diodes. <i>Journal of Applied Physics</i> , <b>2012</b> , 112, 023107	2.5	46
89	Abnormal Stranski-Krastanov Mode Growth of Green InGaN Quantum Dots: Morphology, Optical Properties, and Applications in Light-Emitting Devices. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2019</b> , 11, 1228-1238	9.5	37
88	Fabrication and optical characteristics of phosphor-free InGaN nanopyramid white light emitting diodes by nanospherical-lens photolithography. <i>Journal of Applied Physics</i> , <b>2014</b> , 115, 123101	2.5	31
87	A PMT-like high gain avalanche photodiode based on GaN/AlN periodically stacked structure. <i>Applied Physics Letters</i> , <b>2016</b> , 109, 241105	3.4	30
86	Fabrication and Packaging of 40-Gb/s AlGaInAs Multiple-Quantum-Well Electroabsorption Modulated Lasers Based on Identical Epitaxial Layer Scheme. <i>Journal of Lightwave Technology</i> , <b>2008</b> , 26, 1464-1471	4	29
85	1.55- $\mu\text{m}$ AlGaInAs-InP laterally coupled distributed feedback laser. <i>IEEE Photonics Technology Letters</i> , <b>2005</b> , 17, 1372-1374	2.2	25
84	An InP-based vortex beam emitter with monolithically integrated laser. <i>Nature Communications</i> , <b>2018</b> , 9, 2652	17.4	23
83	A Review on Experimental Measurements for Understanding Efficiency Droop in InGaN-Based Light-Emitting Diodes. <i>Materials</i> , <b>2017</b> , 10,	3.5	23
82	Heterogeneous Integration of Microscale GaN Light-Emitting Diodes and Their Electrical, Optical, and Thermal Characteristics on Flexible Substrates. <i>Advanced Materials Technologies</i> , <b>2018</b> , 3, 1700239	6.8	23
81	Graphene on Self-Assembled InGaN Quantum Dots Enabling Ultrahighly Sensitive Photodetectors. <i>Advanced Optical Materials</i> , <b>2019</b> , 7, 1801792	8.1	22
80	Modulation Characteristics Enhancement of Monolithically Integrated Laser Diodes Under Mutual Injection Locking. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , <b>2015</b> , 21, 628-635	3.8	21

79	Nonselective and smooth etching of GaN/AlGaIn heterostructures by Cl <sub>2</sub> /Ar/BCl <sub>3</sub> inductively coupled plasmas. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2004</b> , 22, 407-412	2.9	19
78	Controllable two-dimensional photonic crystal patterns fabricated by nanosphere lithography. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , <b>2005</b> , 23, 1585		18
77	A novel model on time-resolved photoluminescence measurements of polar InGaIn/GaN multi-quantum-well structures. <i>Scientific Reports</i> , <b>2017</b> , 7, 45082	4.9	17
76	Study on Injection Efficiency in InGaIn/GaN Multiple Quantum Wells Blue Light Emitting Diodes. <i>Applied Physics Express</i> , <b>2008</b> , 1, 021101	2.4	16
75	Green InGaIn Quantum Dots Breaking through Efficiency and Bandwidth Bottlenecks of Micro-LEDs. <i>Laser and Photonics Reviews</i> , <b>2021</b> , 15, 2000406	8.3	16
74	Study on AlN buffer layer for GaN on graphene/copper sheet grown by MBE at low growth temperature. <i>Journal of Alloys and Compounds</i> , <b>2019</b> , 783, 633-642	5.7	16
73	Generation of multiple near-visible comb lines in an AlN microring via (2) and (3) optical nonlinearities. <i>Applied Physics Letters</i> , <b>2018</b> , 113, 171106	3.4	16
72	Phosphor-free nanopillar white light-emitting diodes grown on {101̄1} planes using nanospherical-lens photolithography. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 241107	3.4	15
71	Back-to-Back UTC-PDs With High Responsivity, High Saturation Current and Wide Bandwidth. <i>IEEE Photonics Technology Letters</i> , <b>2013</b> , 25, 136-139	2.2	13
70	Characteristics of hexagonal c-oriented titanium film as the template for GaN epitaxy on glass substrate by electron beam evaporation. <i>Thin Solid Films</i> , <b>2017</b> , 624, 160-166	2.2	10
69	Mixed-Dimensional Vertical Point pn Junctions. <i>ACS Nano</i> , <b>2020</b> , 14, 3181-3189	16.7	10
68	Influence of Residual Facet Reflection on the Eye-Diagram Performance of High-Speed Electroabsorption Modulated Lasers. <i>Journal of Lightwave Technology</i> , <b>2009</b> , 27, 2970-2976	4	10
67	Low-temperature-dependent property in an avalanche photodiode based on GaN/AlN periodically-stacked structure. <i>Scientific Reports</i> , <b>2016</b> , 6, 35978	4.9	9
66	The Influence of Structure Parameter on GaN/AlN Periodically Stacked Structure Avalanche Photodiode. <i>IEEE Photonics Technology Letters</i> , <b>2017</b> , 29, 2187-2190	2.2	9
65	Recent progresses on InGaIn quantum dot light-emitting diodes. <i>Frontiers of Optoelectronics</i> , <b>2014</b> , 7, 293-299	2.8	8
64	MBE Growth of AlN Nanowires on Si Substrates by Aluminizing Nucleation. <i>Nanoscale Research Letters</i> , <b>2015</b> , 10, 383	5	8
63	Atomically smooth and homogeneously N-polar AlN film grown on silicon by aluminization of Si <sub>3</sub> N <sub>4</sub> . <i>Applied Physics Letters</i> , <b>2013</b> , 102, 141913	3.4	8
62	Light extraction improvement of InGaIn light-emitting diodes with large-area highly ordered ITO nanobowls photonic crystal via self-assembled nanosphere lithography. <i>AIP Advances</i> , <b>2013</b> , 3, 092124	1.5	8

61	Laser annealing of SiO <sub>2</sub> film deposited by ICPECVD for fabrication of silicon based low loss waveguide. <i>Frontiers of Optoelectronics</i> , <b>2016</b> , 9, 323-329	2.8	7
60	Study on internal quantum efficiency of blue InGaN multiple-quantum-well with an InGaN underneath layer. <i>Science China Technological Sciences</i> , <b>2010</b> , 53, 306-308	3.5	7
59	Polymer gratings with low surface relief based on photopolymerization-induced internal diffusion. <i>Applied Physics Letters</i> , <b>2004</b> , 84, 3019-3021	3.4	7
58	Transfer-printed, tandem microscale light-emitting diodes for full-color displays. <i>Proceedings of the National Academy of Sciences of the United States of America</i> , <b>2021</b> , 118,	11.5	7
57	Study on Optical Properties and Internal Quantum Efficiency Measurement of GaN-based Green LEDs. <i>Applied Sciences (Switzerland)</i> , <b>2019</b> , 9, 383	2.6	6
56	Study on spin and optical polarization in a coupled InGaN/GaN quantum well and quantum dots structure. <i>Scientific Reports</i> , <b>2016</b> , 6, 35597	4.9	6
55	Sub-THz wave generation based on a dual wavelength microsquare laser. <i>Electronics Letters</i> , <b>2017</b> , 53, 939-941	1.1	6
54	Fabrication of GaN-based ridge waveguides with very smooth and vertical sidewalls by combined plasma dry etching and wet chemical etching. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2015</b> , 212, 2341-2344	1.6	6
53	High-speed (>40 GHz) integrated electroabsorption modulator based on identical epitaxial layer approach. <i>IEEE Photonics Technology Letters</i> , <b>2005</b> , 17, 327-329	2.2	6
52	Theoretical study on critical thickness of heteroepitaxial h-BN on hexagonal crystals. <i>Journal of Crystal Growth</i> , <b>2017</b> , 467, 126-131	1.6	5
51	Ab initio study of GaN periodically substituted by transition metal for intermediate band materials. <i>Physica Status Solidi (B): Basic Research</i> , <b>2011</b> , 248, 964-968	1.3	5
50	Analysis of OAM Mode Purity of Integrated Optical Vortex Beam Emitters. <i>IEEE Photonics Journal</i> , <b>2017</b> , 9, 1-7	1.8	4
49	The influences of sputtered AlN buffer layer on AlInGaN based blue and near-ultraviolet light emitting diodes. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2017</b> , 214, 1600714	1.6	4
48	Study on carrier lifetimes in InGaN multi-quantum well with different barriers by time-resolved photoluminescence. <i>Physica Status Solidi (B): Basic Research</i> , <b>2015</b> , 252, 956-960	1.3	4
47	Linewidth Narrowing of Mutually Injection Locked Semiconductor Lasers with Short and Long Delay. <i>Applied Sciences (Switzerland)</i> , <b>2019</b> , 9, 1436	2.6	3
46	V-shaped semipolar InGaN/GaN multi-quantum-well light-emitting diodes directly grown on c-plane patterned sapphire substrates. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2017</b> , 214, 1600810	1.6	3
45	Edge dislocation induced self-assembly of InGaN nano-flower on GaN by metal organic vapor phase epitaxy. <i>Journal of Applied Physics</i> , <b>2011</b> , 110, 014311	2.5	3
44	Nonlinearity in power-current Characteristics of narrow-pulse-driven AlGaInP laser diodes. <i>IEEE Journal of Quantum Electronics</i> , <b>2004</b> , 40, 349-353	2	3

43	Coherently Combined DFB Laser Array Chip With Reduced Relative Intensity Noise. <i>IEEE Photonics Technology Letters</i> , <b>2021</b> , 33, 986-989	2.2	3
42	Spatial distribution study of a nitrogen plasma in an ion-filtered inductively coupled plasma used to grow GaN films. <i>Journal Physics D: Applied Physics</i> , <b>2019</b> , 52, 395101	3	2
41	Locked and Unlocked Behavior of Integrated Mutually Coupled Lasers with Ultra-Short Delay <b>2014</b> ,		2
40	Growth and characterization of self-assembled low-indium composition InGaN nanodots by alternate admittance of precursors. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2012</b> , 209, 1096-1100	1.6	2
39	The influence of underlying layer on morphology of InGaN quantum dots self-assembled by metal organic vapor phase epitaxy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2012</b> , 9, 782-785		2
38	Resonance Suppression of Grounded Coplanar Waveguide in Submount for 40 Gb/s Optoelectronic Modules. <i>Journal of Infrared, Millimeter, and Terahertz Waves</i> , <b>2009</b> , 30, 103-108	2.2	2
37	High-Speed Coplanar Waveguide Based Submount for 40 Gbit/s Electroabsorption Modulator. <i>Journal of Infrared, Millimeter and Terahertz Waves</i> , <b>2005</b> , 26, 1491-1500		2
36	InP-based optoelectronic devices for optical fiber communications. <i>European Physical Journal D</i> , <b>1999</b> , 49, 751-756		2
35	Studies on Carrier Recombination in GaN/AlN Quantum Dots in Nanowires with a Core-Shell Structure. <i>Nanomaterials</i> , <b>2020</b> , 10,	5.4	2
34	Transferable InGaN Quantum Well Grown at Low Temperature on Amorphous Substrates by Plasma-Assisted Molecular Beam Epitaxy. <i>Crystal Growth and Design</i> , <b>2021</b> , 21, 3831-3837	3.5	2
33	An InP-Based Mid-Wave Infrared Up-Converter Utilizing Cascade Carrier Transportation. <i>IEEE Photonics Technology Letters</i> , <b>2016</b> , 28, 1371-1374	2.2	2
32	Size-dependent optical properties of InGaN quantum dots in GaN nanowires grown by MBE. <i>Frontiers of Optoelectronics</i> , <b>2016</b> , 9, 318-322	2.8	2
31	D-Band MUTC Photodiodes With Flat Frequency Response. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , <b>2021</b> , 1-1	3.8	2
30	A simple fabrication process for SiNx/SiO <sub>2</sub> waveguide based on sidewall oxidation of patterned silicon substrate. <i>Journal of Modern Optics</i> , <b>2017</b> , 64, 226-230	1.1	1
29	Detectivity Enhancement in Cascade Infrared Upconverter Utilizing AlInP Hole-Blocking Layer. <i>IEEE Photonics Technology Letters</i> , <b>2017</b> , 29, 905-908	2.2	1
28	Gain-Coupled 4 × 25 Gb/s EML Array Based on an Identical Epitaxial Layer Integration Scheme. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , <b>2019</b> , 25, 1-6	3.8	1
27	1.3 μm 10-Wavelength Laterally Coupled Distributed Feedback Laser Array with High-Duty-Ratio Gratings. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2018</b> , 216, 1800490	1.6	1
26	The Effect of Inductively Coupled Plasma Etching on the I <sub>V</sub> Curves of the Avalanche Photodiode with GaN/AlN Periodically Stacked Structure. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2019</b> , 216, 1900655	1.6	1

25	Optical generation of microwave carrier with high spectral purity using integrated dual wavelength semiconductor laser diode <b>2010</b> ,		1
24	Optimization of material structure of ploy-Si thin film based on Al induced crystallization. <i>Science in China Series D: Earth Sciences</i> , <b>2009</b> , 52, 2186-2189		1
23	Phase noise characteristics of optically generated microwave by sideband injection locking <b>2008</b> ,		1
22	The design and fabrication of nanostructure on p-type GaN surface for GaN-based LEDs with high light extraction efficiency <b>2007</b> ,		1
21	Experimental Study on the Modulation Nonlinearity of DFB Laser and DFB/EA Integrated Device <b>2007</b> ,		1
20	Novel low-cost wideband Si-based submount for 40 Gb/s optoelectronic devices. <i>Microwave and Optical Technology Letters</i> , <b>2005</b> , 45, 90-93	1.2	1
19	Analysis of the Chirped Super Moiré Gratings Based on Acousto-Optical Superlattices. <i>Journal of Infrared, Millimeter and Terahertz Waves</i> , <b>2000</b> , 21, 939-944		1
18	A Directly Modulated Laterally Coupled Distributed Feedback Laser Array Based on SiO <sub>2</sub> Planarization Process. <i>Applied Sciences (Switzerland)</i> , <b>2021</b> , 11, 221	2.6	1
17	Broadband Meandered Thin-film Lithium Niobate Modulator with Ultra-low Half-wave Voltage. <i>IEEE Photonics Technology Letters</i> , <b>2022</b> , 1-1	2.2	1
16	Capacitively-loaded Thin-film Lithium Niobate Modulator with Ultra-flat Frequency Response. <i>IEEE Photonics Technology Letters</i> , <b>2022</b> , 1-1	2.2	1
15	Van der Waals coherent epitaxy of GaN and InGaN/GaN multi-quantum-well via a graphene inserted layer. <i>Optical Materials Express</i> , <b>2021</b> , 11, 4118	2.6	0
14	Investigation of Microcrystalline Silicon Thin Film Fabricated by Magnetron Sputtering and Copper-Induced Crystallization for Photovoltaic Applications. <i>Applied Sciences (Switzerland)</i> , <b>2020</b> , 10, 6320	2.6	0
13	Gain-Coupled 456 Gb/s EML Array with Optimized Bonding-Wire Inductance. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , <b>2022</b> , 28, 1-7	3.8	0
12	Disk-Shaped GaN Quantum Dots Embedded in AlN Nanowires for Room-Temperature Single-Photon Emitters Applicable to Quantum Information Technology. <i>ACS Applied Nano Materials</i> , <b>2022</b> , 5, 4000-4008	5.6	0
11	Numerical Study of Transient Oscillation in Gain-Switched InGaN-Based Laser Diodes. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , <b>2017</b> , 23, 1-6	3.8	
10	Micro-LEDs: Heterogeneous Integration of Microscale GaN Light-Emitting Diodes and Their Electrical, Optical, and Thermal Characteristics on Flexible Substrates (Adv. Mater. Technol. 1/2018). <i>Advanced Materials Technologies</i> , <b>2018</b> , 3, 1870005	6.8	
9	Strain effect on intersubband transition in a GaN/AlGaIn single quantum well on arbitrary crystal planes. <i>Optical and Quantum Electronics</i> , <b>2018</b> , 50, 1	2.4	
8	Surface Grating Fabrication by Inductively Coupled Plasma Dry Etching for InP-Based Photonic Integrated Circuits. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2018</b> , 215, 1800406	1.6	

- 7 Flat Filter Based on a Chirped Super Moiré Grating. *Journal of Infrared, Millimeter and Terahertz Waves*, **2000**, 21, 1313-1319
- 6 Correction to "Analytical expression of sampled Bragg gratings with chirp in the sampling period and its application on dispersion management design in a WDM system". *IEEE Photonics Technology Letters*, **2001**, 13, 388 2.2
- 5 Optical Properties of Diffused AlGaAs/GaAs Multiple Quantum Wells and their Applications in high Power Laser. *Materials Research Society Symposia Proceedings*, **1996**, 450, 395
- 4 DISTRIBUTED FEEDBACK SEMICONDUCTOR LASERS AND THEIR APPLICATION IN PHOTONIC INTEGRATED DEVICES. *International Journal of High Speed Electronics and Systems*, **1996**, 07, 409-428 0.5
- 3 DISTRIBUTED FEEDBACK SEMICONDUCTOR LASERS AND THEIR APPLICATION IN PHOTONIC INTEGRATED DEVICES. *Selected Topics in Electornics and Systems*, **1997**, 69-86 0
- 2 Simple dynamic energy core equivalent rays method to design freeform surface for extended source. *Frontiers of Optoelectronics*, **2016**, 9, 330-337 2.8
- 1 Plasmon-Enhanced Hot-Electron Photodetector Based on Au/GaN-Nanopillar Arrays for Short-Wave-Infrared Detection. *Applied Sciences (Switzerland)*, **2022**, 12, 4277 2.6